

Bipolar Transistor

(-)160 V, (-)1.5 A, Low V_{CE}(sat), (PNP) NPN Single PCP

2SA1419, 2SC3649

Features

- Adoption of FBET, MBIT Processes
- High Breakdown Voltage and Large Current Capacity
- Ultrasmall Size Making it Easy to Provide High-density, Small-sized Hybrid IC's

Specifications

(): 2SA1419

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

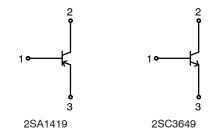
Symbol	Parameter	Conditions	Ratings	Unit
V _{CBO}	Collector-to-Base Voltage	-	(-)180	V
V _{CEO}	Collector-to-Emitter Voltage	-	(-)160	V
V_{EBO}	Emitter-to-Base Voltage	-	(–)6	V
I _C	Collector Current	-	(–)1.5	Α
I _{CP}	Collector Current (Pulse)	-	(-)2.5	Α
Pc	Collector Dissipation	-	500	mW
		When mounted on ceramic substrate (250 mm ² x 0.8 mm)	1.5	V
Tj	Junction Temperature	-	150	°C
Tstg	Storage Temperature	-	–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

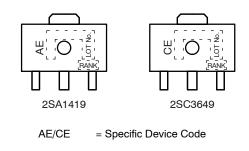


- 1. Base
- Collector
 Emitter
- SOT-89 / PCP-1 CASE 419AU

ELECTRICAL CONNECTIONS



MARKING DIAGRAMS



ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Symbol	Parameter	Conditions	Ratings		Unit	
			Min	Тур	Max	
I _{CBO}	Collector Cutoff Current	V _{CB} = (-)120 V, I _E = 0 A	-	-	(-)1	μΑ
I _{EBO}	Emitter Cutoff Current	V _{EB} = (-)4 V, I _C = 0 A	-	-	(-)1	μΑ
h _{FE} 1	DC Current Gain	$V_{CE} = (-)5 \text{ V}, I_{C} = (-)100 \text{ mA}$	100*	-	400*	
h _{FE} 2		V _{CE} = (-)5 V, I _C = (-)10 mA	80	-	-	
f _T	Gain-Bandwidth Product	$V_{CE} = (-)10 \text{ V}, I_{C} = (-)50 \text{ mA}$	-	120	-	MHz
Cob	Output Capacitance	V _{CB} = (-)10 V, f = 1 MHz	-	(22)14	-	pF
V _{CE} (sat)	Collector-to-Emitter Saturation Voltage	I _C = (-)500 mA, I _B = (-)50 mA	-	(-200) 130	(-500) 450	mV
V _{BE} (sat)	Base-to-Emitter Saturation Voltage	I _C = (-)500 mA, I _B = (-)50 mA	-	(-)0.85	(-)1.2	V
V _{(BR)CBO}	Collector-to-Base Breakdown Voltage	I _C = (-)10 μA, I _E = 0 A	(-)180	-	-	V
V _{(BR)CEO}	Collector-to-Emitter Breakdown Voltage	I _C = (-)1 mA, R _{BE} = ∞	(-)160	-	-	V
V _{(BR)EBO}	Emitter-to-Base Breakdown Voltage	I _E = (-)10 μA, I _C = 0 A	(-)6	-	-	V
t _{on}	Turn-ON Time	See specified Test Circuit	-	(40) 40	-	ns
t _{stg}	Storage Time		-	(0.7) 1.2	-	μs
t _f	Fall Time		-	(40) 80	-	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

* The 2SA1419 / 2SC3649 are classified by 100 mA h_{FE} as follows:

Rank
 R
 S
 T

 h_{FE}
 100 to 200
 140 to 280
 200 to 400

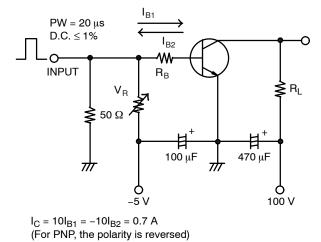
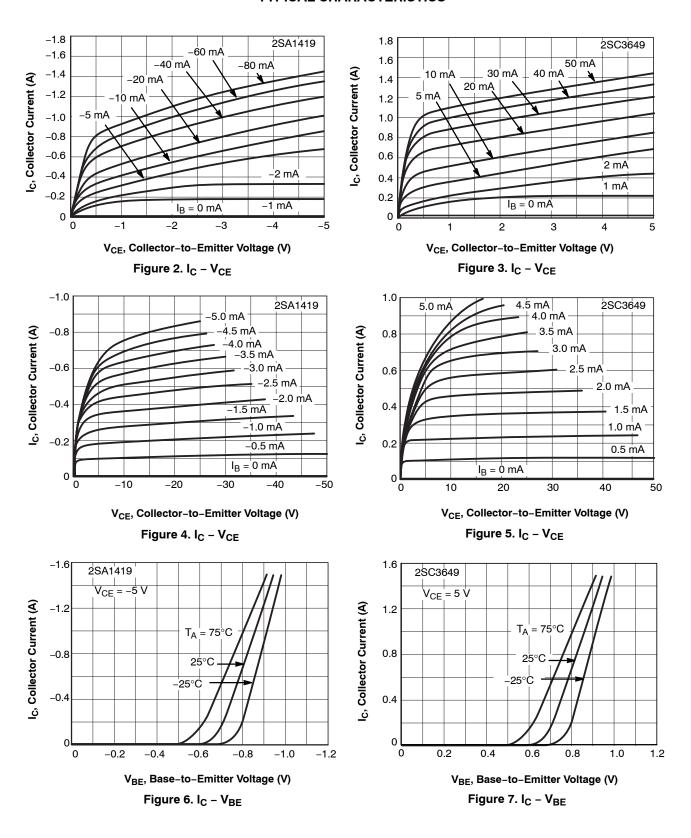


Figure 1. Switching Time Test Circuit

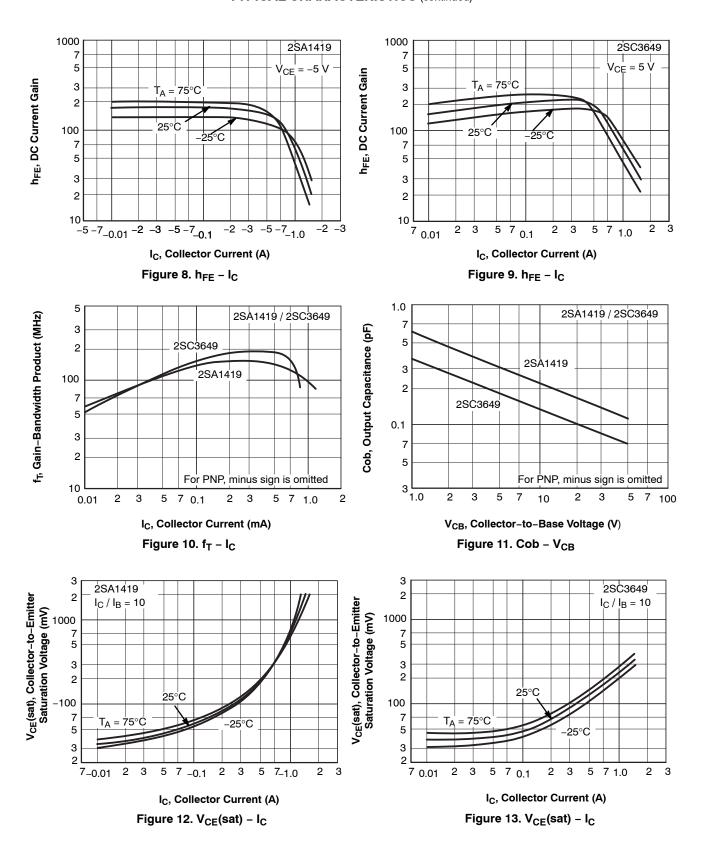
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TYPICAL CHARACTERISTICS



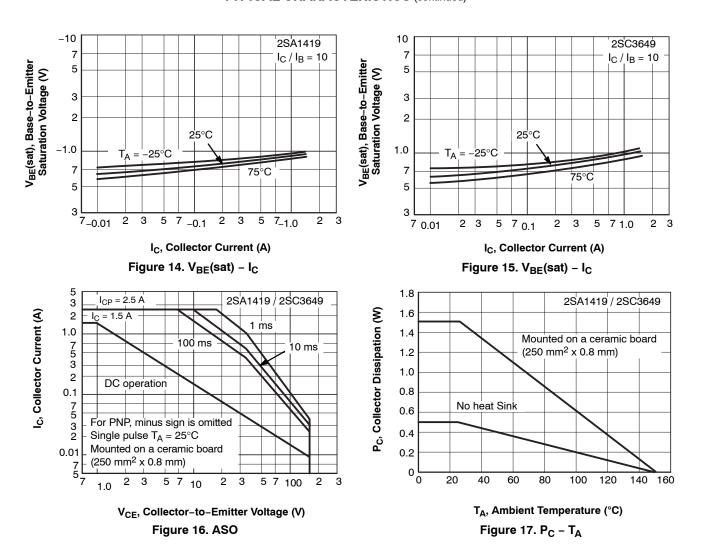
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TYPICAL CHARACTERISTICS (continued)



2SA1419, 2SC3649

TYPICAL CHARACTERISTICS (continued)



ORDERING INFORMATION

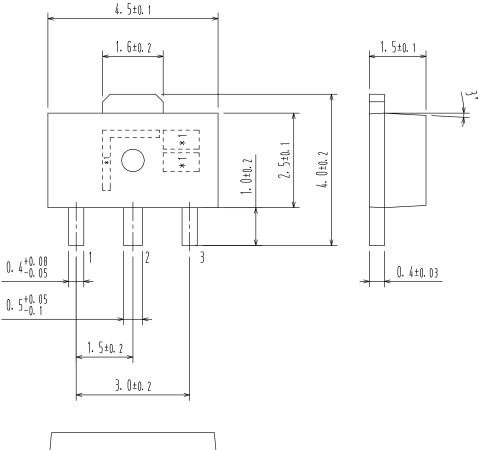
Device	Package	Shipping [†]
2SA1419S-TD-E	SOT-89 / PCP-1 (Pb-Free)	1000 / Tape & Reel
2SA1419T-TD-E	SOT-89 / PCP-1 (Pb-Free)	1000 / Tape & Reel
2SA1419T-TD-H	SOT-89 / PCP-1 (Pb-Free, Halide Free)	1000 / Tape & Reel
2SC3649S-TD-E	SOT-89 / PCP-1 (Pb-Free)	1000 / Tape & Reel
2SC3649S-TD-H	SOT-89 / PCP-1 (Pb-Free & Halogen Free)	1000 / Tape & Reel
2SC3649T-TD-E	SOT-89 / PCP-1 (Pb-Free)	1000 / Tape & Reel
2SC3649T-TD-H	SOT-89 / PCP-1 (Pb-Free & Halogen Free)	1000 / Tape & Reel

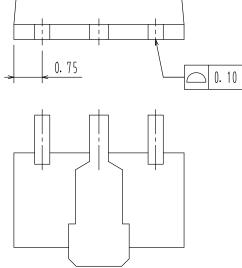
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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DATE 30 APR 2012





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